DATASHEET

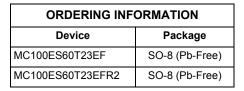
3.3 V Dual Differential LVPECL to **LVTTL Translator**

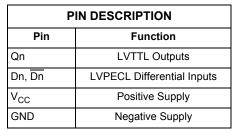
The MC100ES60T23 is a dual differential LVPECL-to-LVTTL translator. The low voltage PECL levels, small package, and dual gate design is ideal for clock translation applications.

Features

- Maximum Frequency 500 MHz
- **Differential LVPECL Inputs**
- LVPECL Operating Range: V_{CC} = 3.0 V to 3.6 V
- Additive Phase Jitter, RMS: 0.18ps (typical)
- 24 mA LVTTL Compatible Outputs
- 8-Lead SOIC Package
- Ambient Temperature Range: -40°C to +85°C
- 8-Lead Pb-Free Package
- Use replacement part: ICS83023I







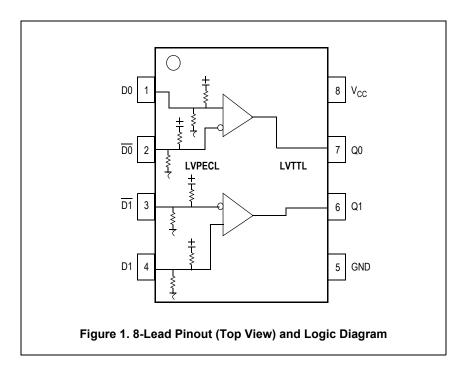




Table 1. General Specifications

Characteristic	Value	
Internal Input Pulldown Resistor	<u>D</u>	75 kΩ 112.5 kΩ
Internal Input Pullup Resistors		75 kΩ
ESD Protection	Human Body Model Machine Model	
θ_{JA} Thermal Resistance (Junction to Ambient)	0 LFPM, 8 SOIC 500 LFPM, 8 SOIC	

Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test

Table 2. Absolute Maximum Ratings⁽¹⁾

Symbol	Parameter	Conditions	Rating	Unit
V _{SUPPLY}	Power Supply Voltage	Difference between V _{CC} and V _{EE}	3.9	V
V _{IN}	Input Voltage	V_{CC} – $V_{EE} \le 3.6 \text{ V}$	V _{CC} + 0.3 V _{EE} - 0.3	V V
I _{OUT}	Output Current	Continuous Surge	50 100	mA mA
T _A	Operating Temperature Range		-40 to +85	°C
T _{STG}	Storage Temperature Range		-65 to +150	°C

^{1.} Absolute maximum continuous ratings are those maximum values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation at absolute-maximum-rated conditions is not implied.

Table 3. LVPECL Input DC Characteristics (V_{CC} = 3.0 to 3.6 V; V_{EE} = 0 V); TA = 40°C to 85°C

Symbol	Characteristic	Min	Тур	Max	Unit
I _{CCH}	Power Supply Current (Outputs set to HIGH)		19	25	mA
I _{CCL}	Power Supply Current (Outputs set to LOW)		6.0	33	mA
V _{IH}	Input HIGH Voltage	V _{CC} -1165		V _{CC} -880	mV
V _{IL}	Input LOW Voltage	V _{CC} -1810		V _{CC} -1475	mV
V _{PP}	Differential Input Voltage ⁽¹⁾	0.15		1.3	V
V _{CMR}	Differential Cross Point Voltage ⁽²⁾	V _{EE} +1.1		V _{CC} -0.65	V
I _{IH}	Input HIGH Current			150	μA
I _{IL}	Input LOW Current	-150			μΑ

^{1.} V_{PP} (DC) is the minimum differential input voltage swing required to maintain device functionality.

^{2.} V_{CMR} (DC) is the crosspoint of the differential input signal. Functional operation is obtained when the crosspoint is within the V_{CMR} (DC) range and the input swing lies within the V_{PP} (DC) specification.



Table 4. LVTTL / LVCMOS Output DC Characteristics (V_{CC} = 3.0 to 3.6 V); TA = 40°C to 85°C

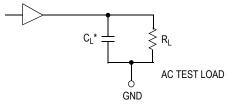
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OH}	Output HIGH Voltage	I _{OH} = -24 mA	2.4			V
V _{OL}	Output LOW Voltage	I _{OL} = 24 mA			0.5	V
Ios	Output Short Circuit Current		-140	-185	-275	mA

Table 5. AC Characteristics (V_{CC} = 3.0 to 3.6 V; V_{EE} = 0 V)⁽¹⁾; TA = 40°C to 85°C

Symbol	Characteristic		Test Conditions	Min	Тур	Max	Unit
f _{OUT}	Output Toggle Frequency ⁽²⁾					500	MHz
t _{PD}	Propagation Delay			0.95		1.75	ns
t _{SK++} t _{SK} t _{SKPP} t _{SKP}	Data Path Skew++ ⁽³⁾ Data Path Skew ⁽³⁾ Part-to-Part Skew ⁽³⁾ Pulse Skew ⁽³⁾					120 140 500 250	ps ps ps ps
t _{JIT}	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section	CLK0/Q0 CLK0/Q0 CLK1/Q1 CLK1/Q1	125MHz, 12kHz - 20MHz 156.25MHz, 12kHz - 20MHz 125MHz, 12kHz - 20MHz 156.25MHz, 12kHz - 20MHz		0.40 0.18 0.38 0.21		ps ps ps ps
V _{PP}	Input Voltage Swing (Differential) ⁽⁴⁾			200		1300	mV
V _{CMR}	Differential Cross Point Voltage			V _{EE} +1.2		V _{CC} -0.3	V
t _r / t _f	Output Rise/Fall Times (0.8 V – 2.0 V)			50		250	ps

- 1. LVTTL output R_L = 500 Ω to GND and C_L = 20 pF to GND. Refer to Figure 2.
- 2. f_{max} guaranteed for functionality only. V_{OL} and V_{OH} levels are guaranteed at DC only. 3. Skews are measured between outputs under identical conditions.
- 4. 200 mV input guarantees AC Characteristics.

CHARACTERISTIC TEST



*C_L includes fixtures capacitance

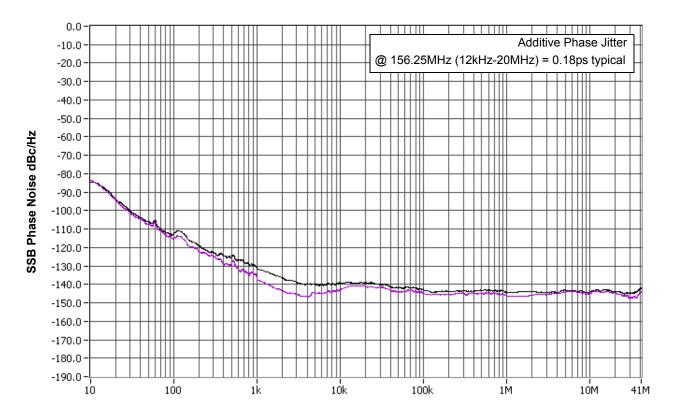
Figure 2. TTL Output Loading Used for Device Evaluation



ADDITIVE PHASE JITTER

The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the dBc Phase Noise. This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels (dBm) or a ratio of the power in the 1Hz band to the power in the

fundamental. When the required offset is specified, the phase noise is called a dBc value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.



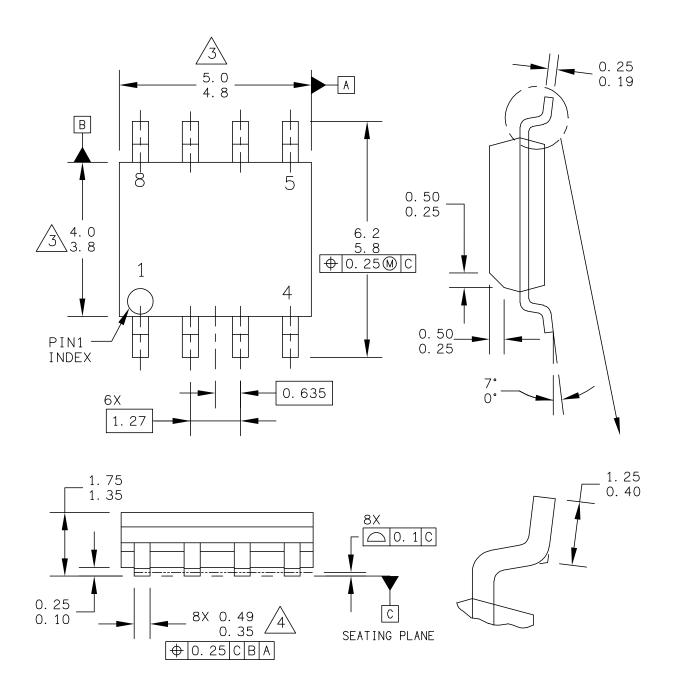
Offset From Carrier Frequency (Hz)

As with most timing specifications, phase noise measurements have issues. The primary issue relates to the limitations of the equipment. Often the noise floor of the equipment is higher than the noise floor of the device. This is

illustrated above. The device meets the noise floor of what is shown, but can actually be lower. The phase noise is dependant on the input source and measurement equipment.



PACKAGE DIMENSIONS



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8LD SOIC NARROW	BODY	CASE NUMBER	2: 751–07	07 APR 2005
		STANDARD: JE	IDEC MS-012AA	

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CASE 751-07 ISSUE U 8-LEAD SOIC PACKAGE



Revision History Sheet

NOTES:

- 1. DIMENSIONS ARE IN MILLIMETERS.
- 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.



3) DIMENSION DOES NOT INCLUDE MOLD PROTRUSION. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.



DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS OF THE DIMENSION AT MAXIMUM MATERIAL CONDITION.

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		STANDARD: JE	DEC MS-012AA	

CASE 751-07 ISSUE U 8-LEAD SOIC PACKAGE PAGE 2 OF 2



Rev	Table	Page	Description of Change	Date
10		1	Product Discontinuance Notice - Last Time Buy Expires on (2/3/13) Use replacement part: ICS83023I	12/14/12



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